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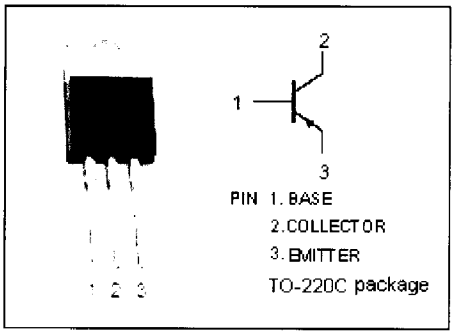
Silicon PNP Power Transistor — 2SA1080



DESCRIPTION

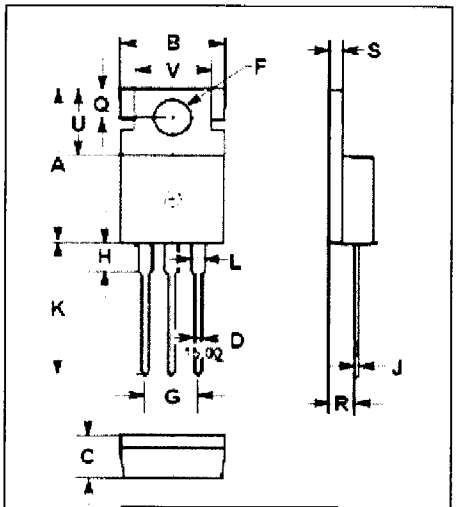
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -40V(Min.)
- Good Linearity of h_{FE}
- Complement to Type 2SC2530

APPLICATIONS

- Designed for medium power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @T_C=25℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; R_{BE}= ∞	-40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -0.1μ A; I_E= 0	-40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -0.1μ A; I_C= 0	-7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -10mA; I_B= -1mA			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -10mA; I_B= -1mA			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-100	nA
I_{CEO}	Collector Cutoff Current	V_{CE}= -40V; I_B= 0			-500	nA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-100	nA
h_{FE}	DC Current Gain	I_C= -10mA; V_{CE}= -5V	100		350	
C_{OB}	Outut Capacitance	I_E= 0; V_{CB}= -20V; f= 1.0MHz		65		pF
f_T	Current-Gain—Bandwidth Product	I_C= -10mA;V_{CE}= -10V; f=10MHz		30		MHz